

#### **Description**

The IRFR1018ETRPBF uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

# D S G

#### TO-252-2L (DPAK)

#### **General Features**

 $V_{DS} = 60V I_{D} = 80 A$ 

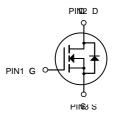
 $R_{DS(ON)}$  < 8.3 m $\Omega$  @  $V_{GS}$ =10V

#### **Application**

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

#### **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
IRFR1018ETRPBF	TO-252-2L(DPAK)	HXY MOSFET	2500

#### Absolute Maximum Ratings (T<sub>C</sub>=25°Cunless otherwise noted)

Symbol	Parameter	Rating		
V <sub>D</sub> s	Drain-Source Voltage	60	V	
Vgs	Gate-Source Voltage	Gate-Source Voltage ±20		
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	us Drain Current, V <sub>GS</sub> @ 10V¹ 80		
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	us Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup> 40		
Ірм	Pulsed Drain Current <sup>2</sup>	255	А	
las	Avalanche Current	Avalanche Current 23		
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation <sup>4</sup>	100	W	
Тѕтс	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	
R <sub>θ</sub> JA	Thermal Resistance Junction-Ambient <sup>1</sup>	62.5	°C/W	



# Electrical Characteristics@Tj=25°C(unless otherwise specified)

	<u>`</u>	<u> </u>				
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	-	-	>
Rds(on)	Static Drain-Source On- Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =45A	-	6	8.3	mΩ
		V <sub>GS</sub> =6V, I <sub>D</sub> =30A	-	13	17	mΩ
V <sub>G</sub> S(th)	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	1.4	3	<b>&gt;</b>
<b>g</b> fs	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =30A	-	71	-	S
Ioss	Drain-Source Leakage Current	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	-	-	10	uA
	Drain-Source Leakage Current (T <sub>j</sub> =125°C)	V <sub>DS</sub> =48V ,V <sub>GS</sub> =0V	-	-	250	uA
Igss	Gate-Source Leakage	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Qg	Total Gate Charge	I <sub>D</sub> =30A	-	33	45	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =48V	-	5	-	nC
$Q_{gd}$	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =4.5V	-	21	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =30V	-	10	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =30A	-	43	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω	-	47	-	ns
t <sub>f</sub>	Fall Time	V <sub>GS</sub> =10V	-	80	-	ns
Ciss	Input Capacitance		-	2680	3300	pF
Coss	Output Capacitance	V <sub>GS</sub> =0V	-	260	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	V <sub>DS</sub> =25V f=1.0MHz	-	180	-	pF
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =45A, V <sub>GS</sub> =0V	-	-	1.3	٧
t <sub>rr</sub>	Reverse Recovery Time	I <sub>S</sub> =10A, V <sub>GS</sub> =0V, dI/dt=100A/μs	-	30	_	ns
Qrr	Reverse Recovery Charge		-	18	-	nC
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# **Typical Performance Characteristics**

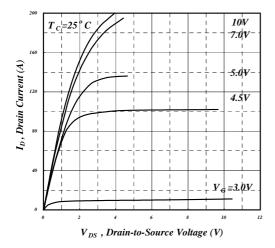


Fig 1. Typical Output Characteristics

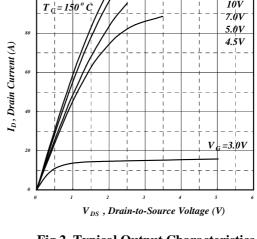


Fig 2. Typical Output Characteristics

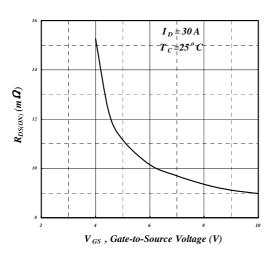


Fig 3. On-Resistance v.s. Gate Voltage

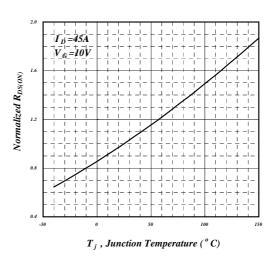


Fig 4. Normalized On-Resistance v.s. Junction Temperature

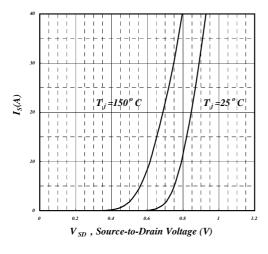


Fig 5. Forward Characteristic of Reverse Diode

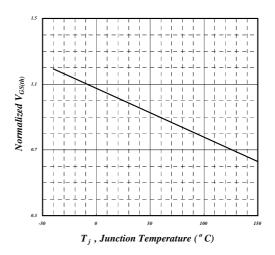


Fig 6. Gate Threshold Voltage v.s.
Junction Temperature

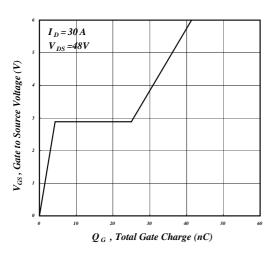


Fig 7. Gate Charge Characteristics

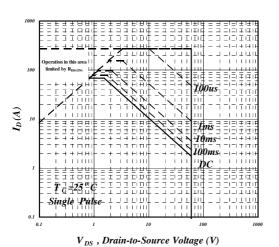


Fig 9. Maximum Safe Operating Area

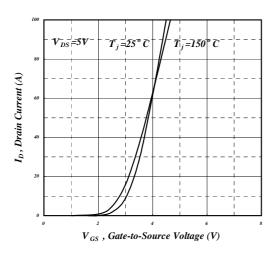


Fig 11. Transfer Characteristics

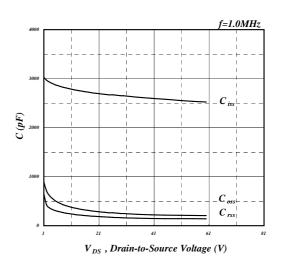


Fig 8. Typical Capacitance Characteristics

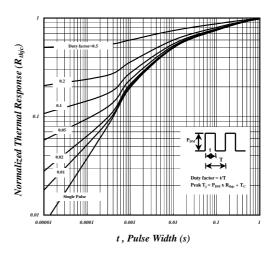


Fig 10. Effective Transient Thermal Impedance

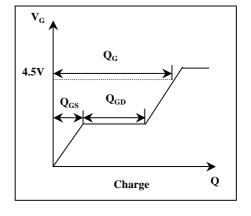
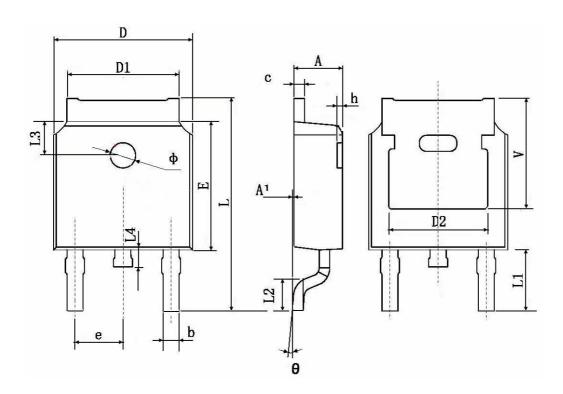


Fig 12. Gate Charge Waveform

### N-Channel Enhancement Mode MOSFET

# TO-252-2L(DPAK) Package Information



Comphal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	0.483 TYP.		0.190 TYP.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350 TYP.		0.211 TYP.		



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